

Prob. Set 6 Solutions from Instructor's Manual for Fund. of EE by Bobrow
 © 1996 by Oxford University Press (except Prob. 6.16).

6.8 Si has 5×10^{23} atoms/m³. $n_i = 1.5 \times 10^{16} \text{ m}^{-3}$ $T = 300 \text{ K}$
 $\mu_n = 0.13 \text{ m}^2/\text{V}\cdot\text{s}$ $\mu_p = 0.05 \text{ m}^2/\text{V}\cdot\text{s}$

For p-type semiconductor:

$$\sigma = p \mu_p q \Rightarrow p = \frac{\sigma}{\mu_p q} = \frac{20.8}{(0.05)(1.6 \times 10^{-19})} = 2.6 \times 10^{21} \text{ m}^{-3}$$

Also $N_A \approx p = 2.6 \times 10^{21} \text{ m}^{-3} \Rightarrow n = \frac{n_i^2}{N_A} = \frac{(1.5 \times 10^{16})^2}{2.6 \times 10^{21}} = 2.4 \times 10^{17} \text{ m}^{-3}$

$$N_A = 5 \times 10^{23} \left(\frac{x}{10^8}\right) = 2.6 \times 10^{21} \Rightarrow x = \frac{2.6 \times 10^{21}}{5 \times 10^{20}} = 5.2 \text{ parts per } 10^8$$

6.16 Find $V_0 = V_T \ln \frac{N_A N_D}{n_i^2}$.

Ge: $\sigma_p = 50 \text{ } \Omega/\text{m}$, $\sigma_n = 100 \text{ } \Omega/\text{m}$

$T = 300 \text{ K}$, $n_i = 2.5 \times 10^{19} \text{ m}^{-3}$

$\mu_p = 0.18 \text{ m}^2/\text{V}\cdot\text{s}$, $\mu_n = 0.38 \text{ m}^2/\text{V}\cdot\text{s}$

For p-type semiconductor, $p = N_A$

$$\sigma_p \approx p \mu_p q = N_A \mu_p q$$

$$N_A \approx \frac{\sigma_p}{\mu_p q} = \frac{50 \text{ } \Omega/\text{m}}{0.18 \text{ m}^2/\text{V}\cdot\text{s} \times 1.6 \times 10^{-19} \text{ C}} = 1.74 \times 10^{21} \text{ m}^{-3}$$

Similarly, $N_D \approx \frac{\sigma_n}{\mu_n q} = \frac{100 \text{ } \Omega/\text{m}}{0.38 \text{ m}^2/\text{V}\cdot\text{s} \times 1.6 \times 10^{-19} \text{ C}} = 1.64 \times 10^{21} \text{ m}^{-3}$

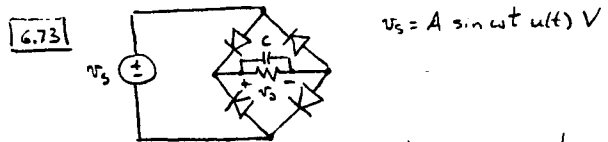
$$V_0 = 26 \text{ mV} \times \ln \frac{1.74 \times 10^{21} \times 1.64 \times 10^{21}}{(2.5 \times 10^{19})^2} = 0.22 \text{ V}$$

6.21 Si diode $i = 20 \text{ mA}$, $v = 0.8 \text{ V}$
 $\eta = 2$ $T = 300 \text{ K}$

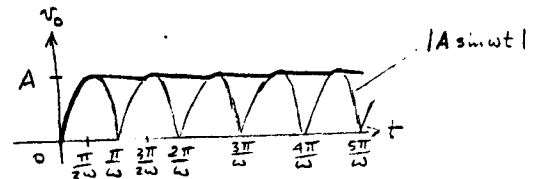
$$i = I_s (e^{v/\eta V_T} - 1) \quad \eta = \frac{T}{11,586}$$

$$I_s = \frac{i}{e^{v/\eta V_T} - 1}$$

(a) $T = 300 \text{ K} \Rightarrow I_s = \frac{20 \text{ mA}}{e^{0.8 / (2 \times 300 / 11,586)} - 1} = 3.91 \text{ } \mu\text{A}$

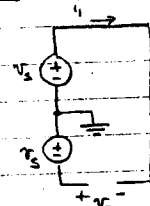


The first time that v_s goes to A volts, the capacitor will charge to $v_o = A$ volts. Since $RC \gg T = 2\pi/\omega$, the capacitor will remain charged at approximately A volts as shown below:



6.74 Same solution as Problem 6.73.

6.45 (a) For $v_s > 0$, assume that D_1 ON, D_2 OFF. Then



By KVL, $v_o = v_s$

Since $v_s > 0$, then

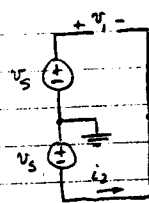
$$i_1 = \frac{v_o}{R} = \frac{v_s}{R} > 0 \Rightarrow D_1 \text{ indeed ON}$$

By KVL, $v_2 = -v_s - v_s = -2v_s$

Since $v_s > 0$, then $-v_s < 0$

$$\therefore v_2 = -2v_s < 0 \Rightarrow D_2 \text{ indeed OFF}$$

(b) For $v_s < 0$, assume that D_1 OFF, D_2 ON. Then



By KVL, $v_o = -v_s$

Since $v_s < 0$, then $-v_s > 0$

$$i_2 = \frac{v_o}{R} = \frac{-v_s}{R} > 0 \Rightarrow D_2 \text{ indeed ON}$$

By KVL, $v_1 = v_s + v_s = 2v_s$

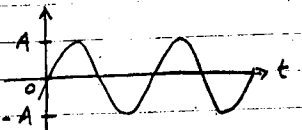
Since $v_s < 0$, then $2v_s < 0$

$$\therefore v_1 = 2v_s < 0 \Rightarrow D_1 \text{ indeed OFF}$$

In summary,

$$v_o = \begin{cases} v_s & \text{for } v_s > 0 \text{ V} \\ -v_s & \text{for } v_s < 0 \text{ V} \end{cases}$$

$$v_s = A \sin \omega t$$



$$v_o = |A \sin \omega t|$$

